NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI PT9733** is an NPN power transistor designed for 25 V Class-C ground station transmitters, it utilizes emitter ballasting and gold metalization to provide optimum VSWR capability.

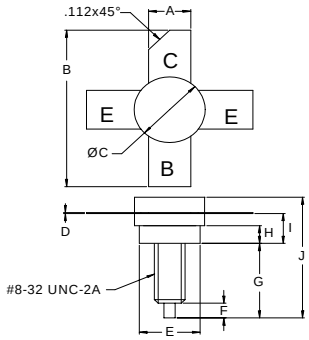
FEATURES:

- Common Emitter
- P_G = 6.0 dB at 50 W/175 MHz
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	8.0 A
V_{CES}	60 V
V_{EBO}	4.0 V
P_{DISS}	85 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.1 °C/W

PACKAGE STYLE .380 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 25 mA			35			V
BV_{CES}	I_C = 50 mA			60			V
BV_{EBO}	I_E = 8.0 mA			4.0			V
I_{CES}	V_{CE} = 25 V					2.0	mA
h_{FE}	V_{CE} = 10 V	I_C = 500 mA		20		150	---
C_{ob}	V_{CB} = 28 V		f = 1.0 MHz			90	Pf
P_G	V_{CE} = 28 V	P_{OUT} =50 W	f = 175 MHz	6.0		6.0	dB
η_C	P_{IN} = 10 W			60		60	%
VSWR						∞	---